

Abstract of the Disclosure

02/318,073

A monolithically formed ferromagnetic thin-film memory is disclosed that has local shielding on at least two sides of selected magnetic storage elements. The local shielding preferably extends along the back and side surfaces of a word line and/or digital lines of a conventional magnetic memory. In this configuration, the local shielding not only may help reduce externally generated EMI, internally generated cross-talk and other unwanted fields in the magnetic bit region, but may also help enhance the desired magnetic fields in the bit region.

CERTIFICATE UNDER 37 CFR 110: The undersigned hereby certifies that this paper or papers, as described hereinabove, are being deposited in the United States Postal Service, "Express Mail Post Office to Addressee" having an Express Mail Mailing label number of:

EL085667322US

in an envelope addressed to:
Assistant Commissioner for Patents
Washington, DC 20231

on this 25th day of May 19 99
Crompton, Seager & Tufte, LLC

By:

Jolene Alger